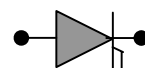


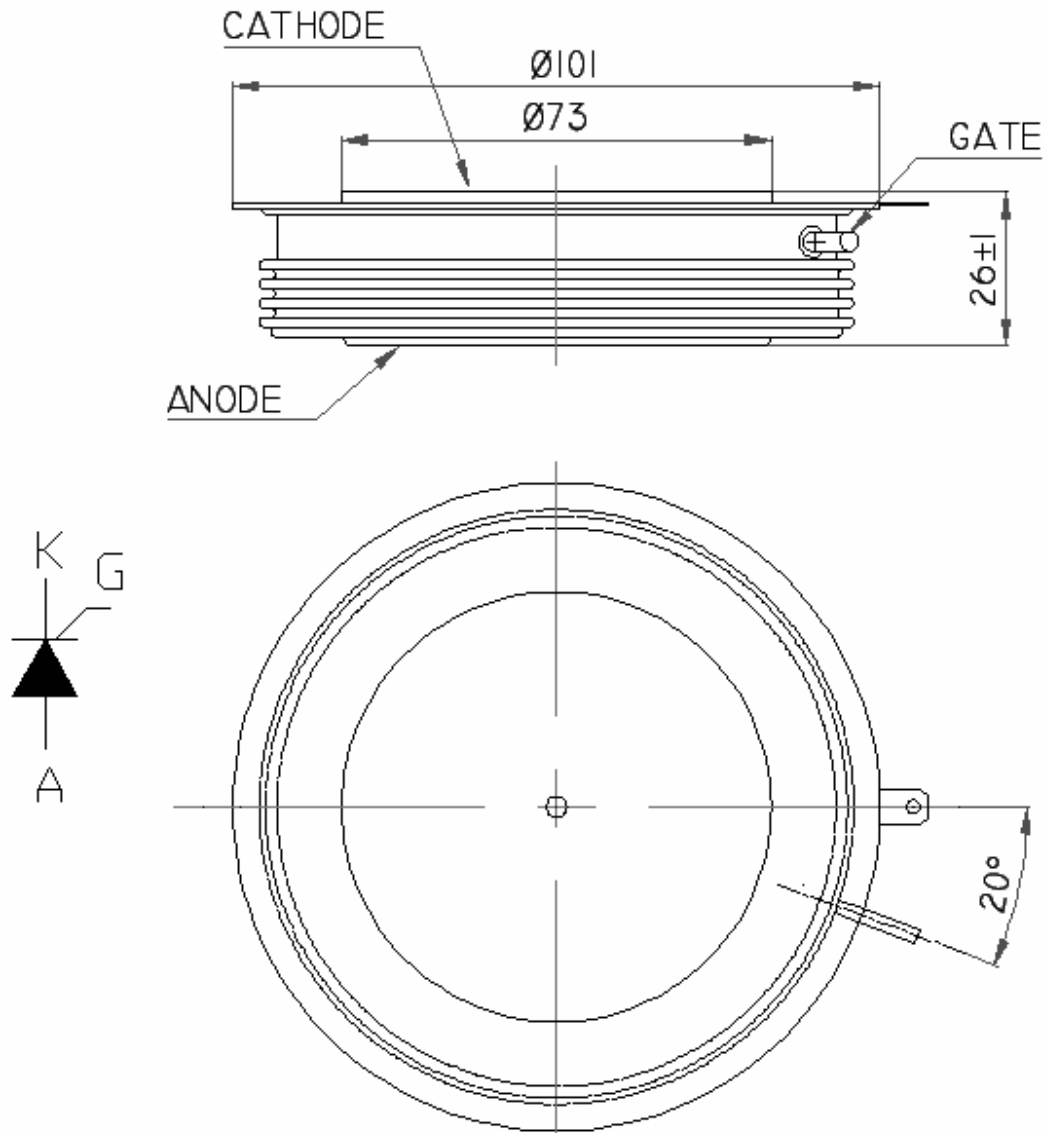
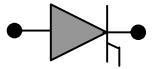
PHASE CONTROL THYRISTOR H4350CHXX



Symbol	Characteristics	Conditions	T_J ($^{\circ}\text{C}$)	Value	Unit
BLOCKING PARAMETERS					
V_{RRM}	Repetitive peak reverse voltage		125	200-1200	V
V_{DRM}	Repetitive peak off-stage voltage		125	200-1200	V
I_{RRM}	Repetitive peak reverse current	$V = V_{RRM}$	125	200	mA
I_{DRM}	Repetitive peak off-state current	$V = V_{RRM}$	125	200	mA
CONDUCTING PARAMETERS					
$I_{F(AV)}$	Average on-state current	180 sine, 50Hz, $T_C = 55^{\circ}\text{C}$		4350	A
I_{RMS}	RMS on-state current			6829	A
I_{TSM}	Surge on-state current	Sine wave, 10mS without reverse voltage	125	60	kA
I^2t	I^2t			18000	kA^2S
V_T	Peak on-state voltage drop	On-state current = 4kA	125	1.18	V
V_0	Threshold voltage		125	0.88	V
R_0	On-state slope resistance		125	0.075	$\text{m}\Omega$
TRIGGERING PARAMETERS					
I_{GT}	Gate trigger current	$V_D = 5\text{V}$	25	350	mA
V_{GT}	Gate trigger voltage		25	2.00	V
I_H	Holding Current	$V_D = 5\text{V}$	25	300	mA
I_L	Latching Current	$V_D = 5\text{V}$	25	700	mA
di/dt	Repetitive rate of rise of current			200	$\text{A}/\mu\text{Sec}$
THERMAL & MECHANICAL PARAMETERS					
$R_{TH(J-C)}$	Thermal impedance, 180 conduction, Sine	Junction to heatsink		.0095	$^{\circ}\text{C}/\text{W}$
$R_{TH(C-HK)}$	Thermal impedance	Case to heatsink		0.002	$^{\circ}\text{C}/\text{W}$
T_J	Maximum Permissible junction temperature			125	$^{\circ}\text{C}$
T_{STG}	Storage temperature range			-30 - 125	$^{\circ}\text{C}$
F	Mounting Torque			40-50	KN
W	Weight			1150	gms



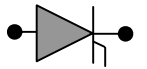
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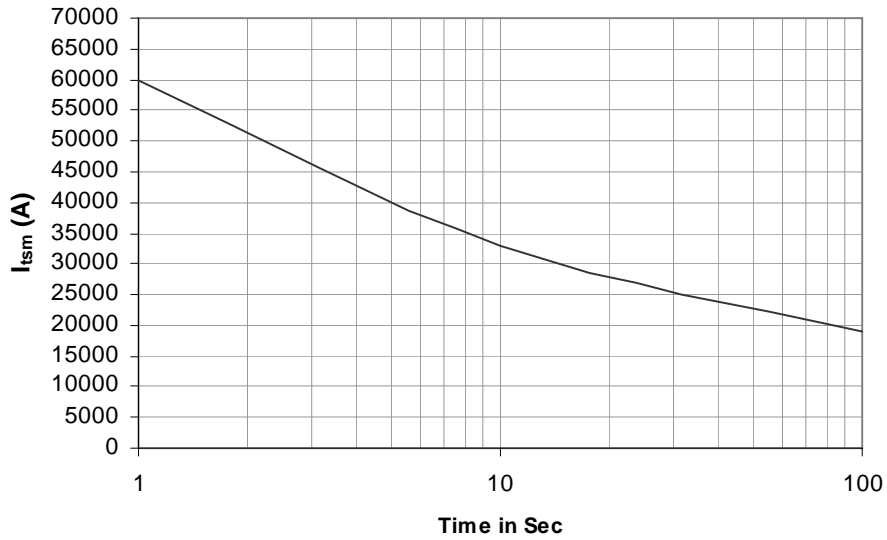
All dimensions in mm



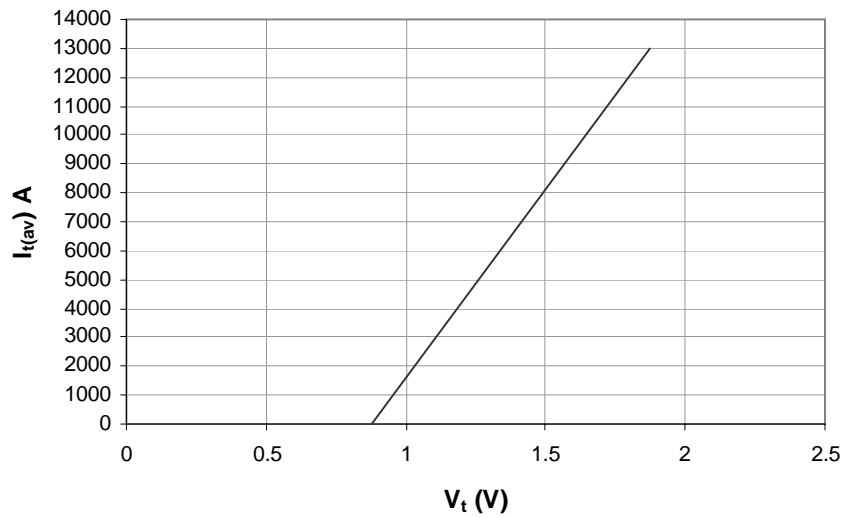
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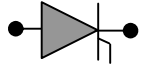


Max non repetitive Surge Current

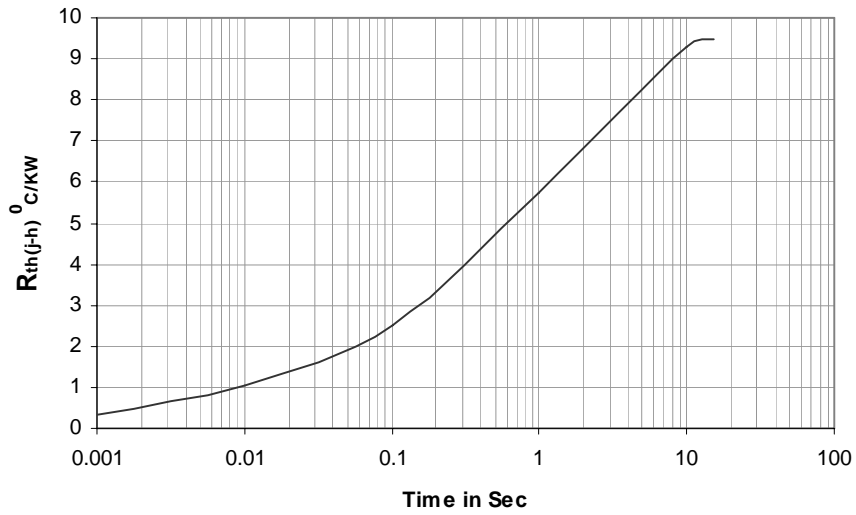


On State Characteristics

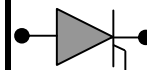




Transient Thermal Impedance Junction to Case



PHASE CONTROL THYRISTOR H4350CHXX



Ordering Information: -

H	4350	CH	XX
Hirect make Thyristor	$I_{F(AV)} = 4350A$	Capsule Thyristor	$V_{RRM} = XX * 100$ e.g. $12 * 100 = 1200V$

Hind Rectifiers Ltd reserves the right to change the specifications without notice.

This datasheet specifies technical information for semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

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June-2008



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